Konrad Sakowski

List of Publications by Year
in descending order

37	382	840776 11	839539 18
papers	citations	h-index	g-index

39	39	39	380
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Al coverage of AlN(0001) surface and Al vapor pressure â€“ Thermodynamic assessment based on ab initio calculations. Computational Materials Science, 2022, 203, 111159.	3.0	0
2	Relevance of intra-hospital patient movements for the spread of healthcare-associated infections within hospitals - a mathematical modeling study. PLoS Computational Biology, 2021, 17, e1008600.	3.2	15
3	Effects of incomplete inter-hospital network data on the assessment of transmission dynamics of hospital-acquired infections. PLoS Computational Biology, 2021, 17, e1008941.	3.2	3
4	Critical Evaluation of Various Spontaneous Polarization Models and Induced Electric Fields in III-Nitride Multi-Quantum Wells. Materials, 2021, 14, 4935.	2.9	6
5	Adsorption of nitrogen at AlN(000-1) surface â€“ Decisive role of structural and electronic factors. Surface Science, 2021, 713, 121891.	1.9	2
6	Impact of inter-hospital transfers on the prevalence of resistant pathogens in a hospitalâ€“community system. Epidemics, 2020, 33, 100408.	3.0	7
7	Ab initio and thermodynamic picture of Al adsorption of AlN(0001) surface â€“ Role of bond creation and electron transition contributions. Applied Surface Science, 2020, 532, 147419.	6.1	4
8	Instantaneous decay rate analysis of time resolved photoluminescence (TRPL): Application to nitrides and nitride structures. Journal of Alloys and Compounds, 2020, 823, 153791.	5.5	5
9	Modelling pathogen spread in a healthcare network: Indirect patient movements. PLoS Computational Biology, 2020, 16, e1008442.	3.2	8
10	Catalytic Synthesis of Nitric Monoxide at the AlN(0001) Surface: Ab Initio Analysis. Journal of Physical Chemistry C, 2019, 123, 10893-10906.	3.1	4
11	Chemical inactivity of GaN(0001) surface â€“ The role of oxygen adsorption â€“ Ab initio picture. Materials Science in Semiconductor Processing, 2019, 91, 252-259.	4.0	8
12	Analysis of the AOK Plus data and derived hospital network. Mathematica Applicanda, 2019, 47, .	0.0	3
13	Adsorption of N2 and H2 at AlN(0001) Surface: Ab Initio Assessment of the Initial Stage of Ammonia Catalytic Synthesis. Journal of Physical Chemistry C, 2018, 122, 20301-20311.	3.1	9
14	Ab initio determination of electron affinity of polar nitride surfaces, clean and under Cs coverage. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	19
15	Ab initio and experimental studies of polarization and polarization related fields in nitrides and nitride structures. AIP Advances, 2017, 7, .	1.3	23
16	Thermodynamics of GaN(s)-NH 3 (v)+N 2 (v)+H 2 (v) system â€“ Electronic aspects of the processes at GaN(0001) surface. Surface Science, 2017, 662, 12-33.	1.9	12
17	Dissipation of the excess energy of the adsorbate-thermalization via electron transfer. Physical Chemistry Chemical Physics, 2017, 19, 9149-9155.	2.8	4
18	Thermodynamic foundations of applications of ab initio methods for determination of the adsorbate equilibria: hydrogen at the GaN(0001) surface. Physical Chemistry Chemical Physics, 2017, 19, 29676-29684.	2.8	14

#	Article	IF	Citations
19	Discretization of the Drift-Diffusion Equations with the Composite Discontinuous Galerkin Method. Lecture Notes in Computer Science, 2016, , 391-400.	1.3	1
20	High pressure and time resolved studies of optical properties of n-type doped GaN/AlN multi-quantum wells: Experimental and theoretical analysis. Journal of Applied Physics, 2016, 120, .	2.5	14
21	Correlation of optical and structural properties of GaN/AlN multi-quantum wellsâ€"Ab initio and experimental study. Journal of Applied Physics, 2016, 119, 015703.	2.5	27
22	Electric field dynamics in nitride structures containing quaternary alloy (Al, In, Ga)N. Journal of Applied Physics, 2016, 120, 015702.	2.5	2
23	Influence of pressure on the properties of GaN/AlN multi-quantum wells â€“ Ab initio study. Journal of Physics and Chemistry of Solids, 2016, 93, 100-117.	4.0	8
24	Optimization of InGaN Laser Diodes Based on Numerical Simulations. Acta Physica Polonica A, 2016, 129, A-33-A-35.	0.5	1
25	Structural and electronic properties of AlN(0001) surface under partial N coverage as determined by ab initio approach. Journal of Applied Physics, 2015, 118, .	2.5	16
26	Fermi level pinning and the charge transfer contribution to the energy of adsorption at semiconducting surfaces. Journal of Applied Physics, 2014, 115, 043529.	2.5	21
27	Doping effects in InN/GaN short-period quantum well structuresâ€"Theoretical studies based on density functional methods. Journal of Crystal Growth, 2014, 401, 652-656.	1.5	2
28	Adsorption of gallium on GaN(0001) surface in ammonia-rich conditions: A new effect associated with the Fermi level position. Journal of Crystal Growth, 2014, 401, 78-81.	1.5	4
29	General aspects of the vapor growth of semiconductor crystals â€“ A study based on DFT simulations of the NH3/NH2 covered GaN(0001) surface in hydrogen ambient. Journal of Crystal Growth, 2014, 390, 71-79.	1.5	11
30	Adsorption of ammonia on hydrogen covered GaN(0001) surface â€“ Density Functional Theory study. Journal of Crystal Growth, 2014, 401, 514-517.	1.5	7
31	DFT study of ammonia desorption from the GaN(0001) surface covered with a NH3/NH2 mixture. Journal of Crystal Growth, 2014, 403, 105-109.	1.5	6
32	Modification of the Newtonâ€™s Method for the Simulations of Gallium Nitride Semiconductor Devices. Lecture Notes in Computer Science, 2014, , 551-560.	1.3	2
33	Simulation of trap-assisted tunneling effect on characteristics of gallium nitride diodes. Journal of Applied Physics, 2012, 111, .	2.5	32
34	Numerical analysis of growth kinetics of bulk III-V crystals grown by liquid phase electroepitaxy. Crystal Research and Technology, 2010, 45, 1290-1294.	1.3	3
35	Density Functional Theory (DFT) Simulations and Polarization Analysis of the Electric Field in InN/GaN Multiple Quantum Wells (MQWs). Journal of Physical Chemistry C, 2010, 114, 14410-14416.	3.1	24
36	Ab initio studies of electronic properties of bare GaN(0001) surface. Journal of Applied Physics, 2009, 106, .	2.5	43

#	Article	IF	Citations
37	On the composite discontinuous Galerkin method for simulations of electric properties of semiconductor devices. Electronic Transactions on Numerical Analysis, 0, 51, 75-98.	0.0	4